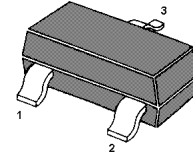


## PNP Silicon Epitaxial Planar Transistor

for high voltage .



1.Base 2.Emitter 3.Collector  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	130	V
Collector Emitter Voltage	$-V_{CEO}$	120	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current Continuous	$-I_C$	600	mA
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-55 to +150	$^\circ\text{C}$

### Characteristics at $T_{amb}=25^{\circ}C$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}=5V, -I_C=10mA$	$h_{FE}$	40	180	-
Collector Base Breakdown Voltage at $-I_C=0.1mA$	$-V_{(BR)CBO}$	130	-	V
Collector Emitter Breakdown Voltage at $-I_C=1mA$	$-V_{(BR)CEO}$	120	-	V
Emitter Base Breakdown Voltage at $-I_E=0.1mA$	$-V_{(BR)EBO}$	5	-	V
Collector Cutoff Current at $-V_{CB}=100V$	$-I_{CBO}$	-	0.05	$\mu A$
Emitter Cutoff Current at $-V_{EB}=3V$	$-I_{EBO}$	-	0.05	$\mu A$
Collector Emitter Saturation Voltage at $-I_C=50mA, -I_B=5mA$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C=50mA, -I_B=5mA$	$-V_{BE(sat)}$	-	1	V
Current Gain Bandwidth Product at $-V_{CE}=10V, -I_C=10mA$	$f_T$	100	-	MHz
Output Capacitance at $-V_{CB}=10V, f=1MHz$	$C_{ob}$	-	6	pF
Noise Figure at $-I_C=0.2mA, -V_{CE}=5V, f=15.7KHz$	NF	-	8	dB